

A (European) Silicon Photonics Platform

Frederic Boeuf , Ph.D.

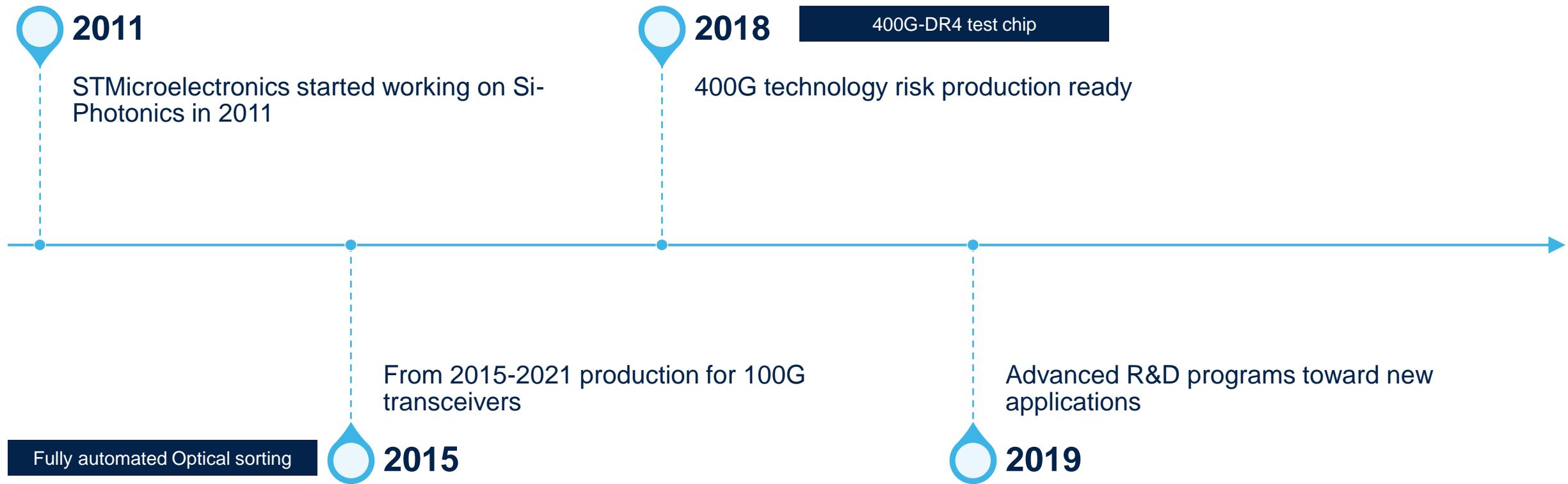
Technical Director

Strategy & Innovation

Technology & Design Platform

STMicroelectronics, Crolles

Si Photonics in STMicroelectronics

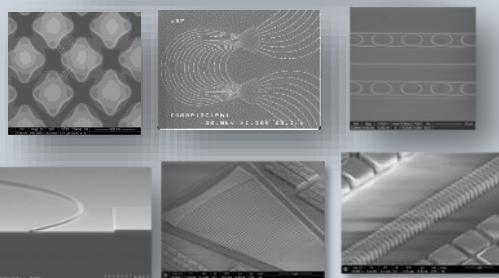
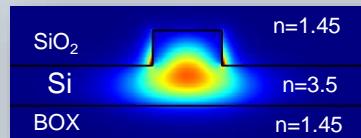
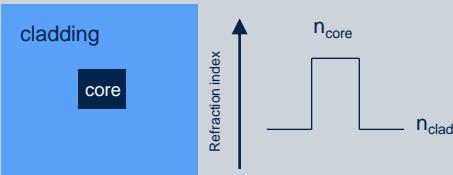


Silicon Photonics Basic Elements

$\lambda = 1.31\mu\text{m}, 1.55\mu\text{m}$

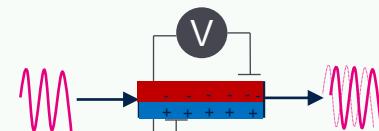
Waveguide

Guiding in high index layer



Modulation

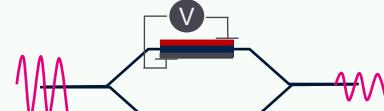
Phase modulation
PN diode or Thermo-optic



$$\Delta n = a\Delta N^x + b\Delta P^y$$

$$\Delta n(V) \rightarrow \Delta\varphi(V) = \frac{2\pi\Delta n L}{\lambda}$$

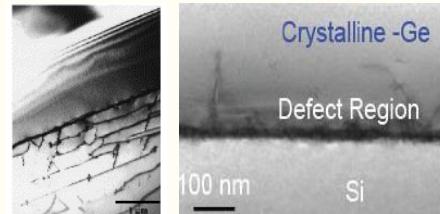
Amplitude modulation



$$I = I_0 \cos^2 \left(\frac{\Delta\varphi}{2} \right)$$

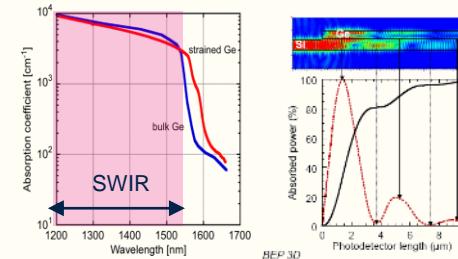
Photodetection

Ge on Si



Currie et al., APL 1998
(MIT)
Nayfeh et al., APL 2004
(Stanford)

Ge absorbs $\lambda < 1.6 \mu\text{m}$

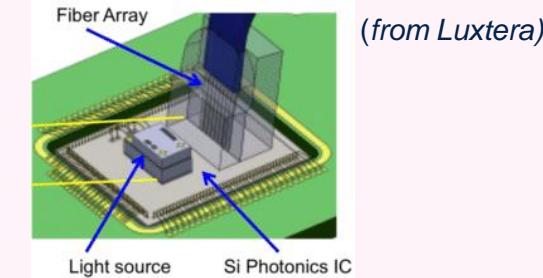


Ge Absorption
in the O,C and
L bands

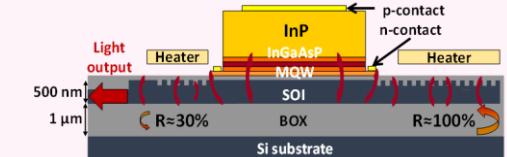
Compact Ge PD
can be
fabricated

Source

External Lasers



Hybrid III-V/Si Lasers



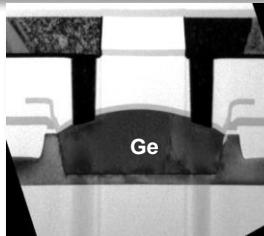
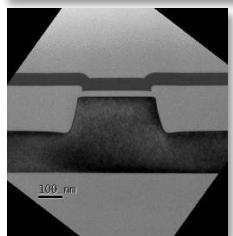
B. Ben Bahkir et al, 2011 (LETI)

Evolution of PIC Platforms at ST

$\lambda = 1.31\mu\text{m}$

100G

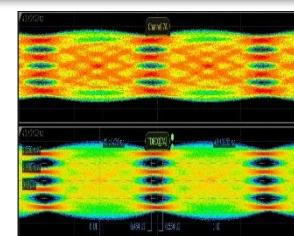
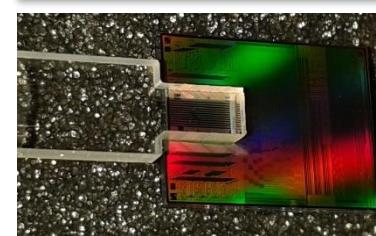
- 300mm / 12"
- NRZ signal
- 20GHz Ge PD
- PN Modulator
- Rib Si-Waveguides
- Grating coupler



F.Bœuf et al. IEDM 2013

400G

- PAM-4 signal 50Gbd/s
- 67 GHz Ge PD
- PN Modulator Gen2
- Si/SiN waveguides
- Thick-Cu Metallization
- Glass Interposer

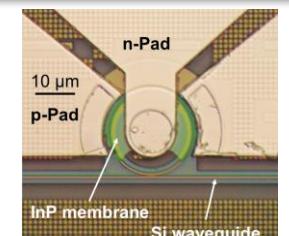
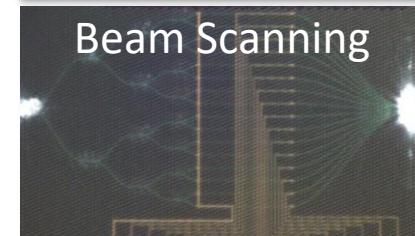


F.Bœuf et al. IEDM 2019

$\lambda = 905\text{nm}, 1.31\mu\text{m}, 1.55\mu\text{m}$

Datacom & Beyond

- PN Modulator Gen3
- Si PD (905nm)
- Si/SiN waveguides
- Low loss Si-Waveguides
- Hybrid III-V/Si Devices^(*)



F.Bœuf et al. IEDM 2021

(*) not in 12"

Si-Photonics : Beyond Datacom

5

DATACOM

Photonic cables connecting people

Bandwidth

Optical Loss

Power Management

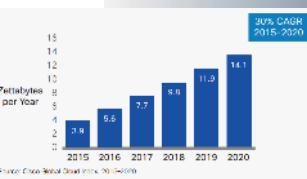
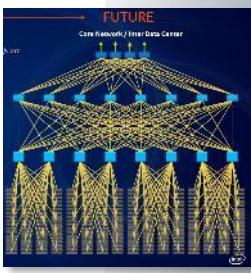
System

Manufacturing

Assembly & Test

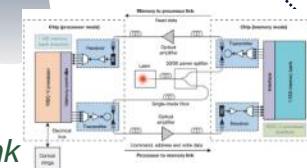
Cost

Footprint



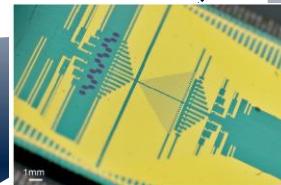
Single Technology

HPC/ONN



*Intra Processor Link
Chen Sun et al.*

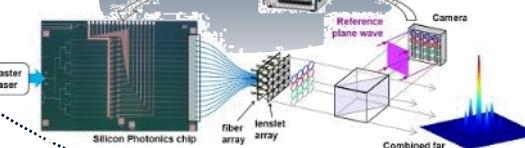
Quantum



Quantum Computing, QKD
Ji Wang et al., Science

Beyond Interconnects
Photonic sensors connecting objects

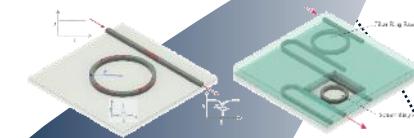
Atmospheric LiDAR
Anemometer
Jérôme Bourderionnet et al.



Depth-Sensing

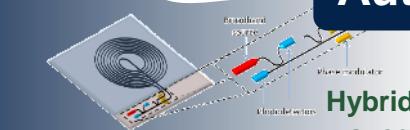
BioSensing

Silicon-Based Optical Biosensors
Laura Lechuga et al.

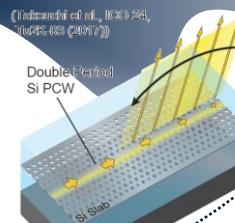


Automotive

Hybrid silicon waveguide optical gyroscope
John Bowers et al.



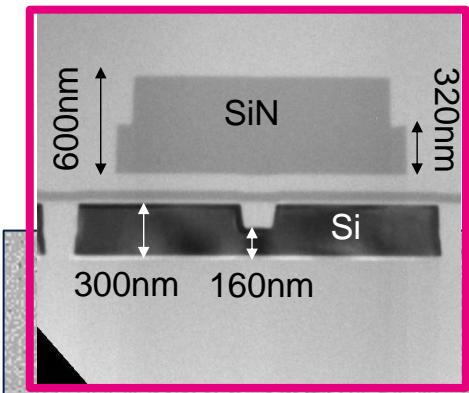
Photonic Crystal based Lidar
T. Baba et al.



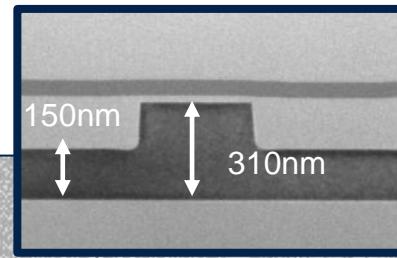
ST Confidential

STMicroelectronics Platform Overview

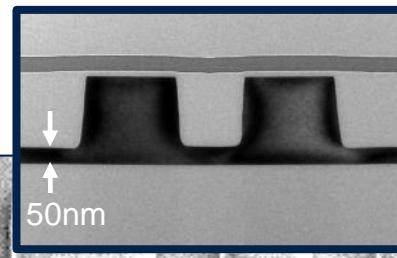
Rib SiN-WG



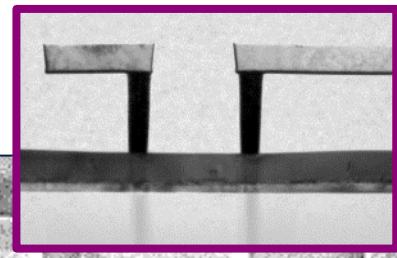
Rib Si-WG



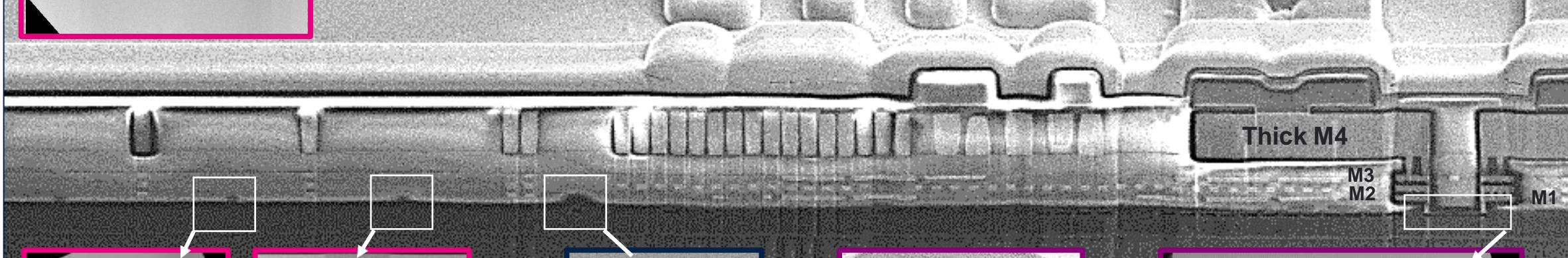
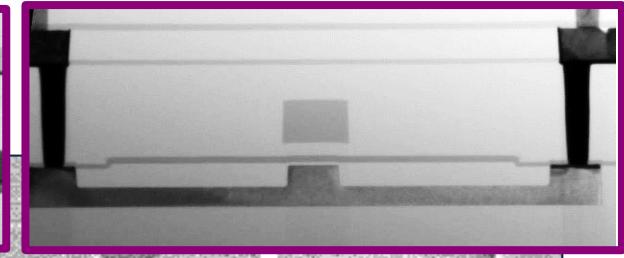
Deep-Rib Si-WG



Ge-HSPD



SiN/Si PD ($\lambda=905\text{nm}$)



Strip SiN-WG

Si-SiN Taper

Si strip WG

TiN heater

Phase Modulators
(PN,PiN,Thermal)

Beam steering for 3D Sensing

3D-Sensing with Silicon Photonics

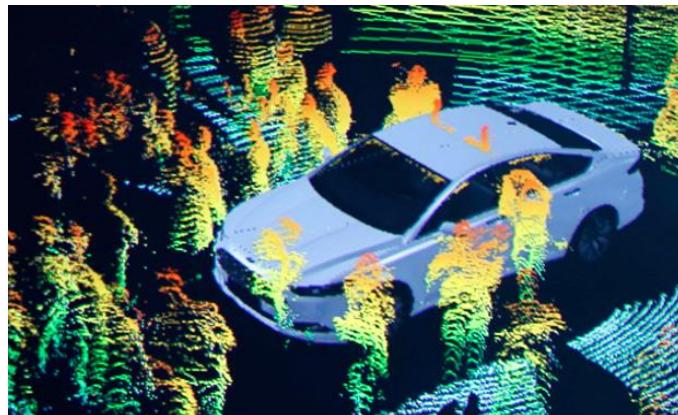


Photo: Jeff Kowalsky/Corbis



<https://3dprint.com/117809/depth-sensing-phone-cameras/>

- Distance measurement (Z-imaging)
 - Up to 200m for automotive : ADAS L3
 - 10-50m for AR/VR applications

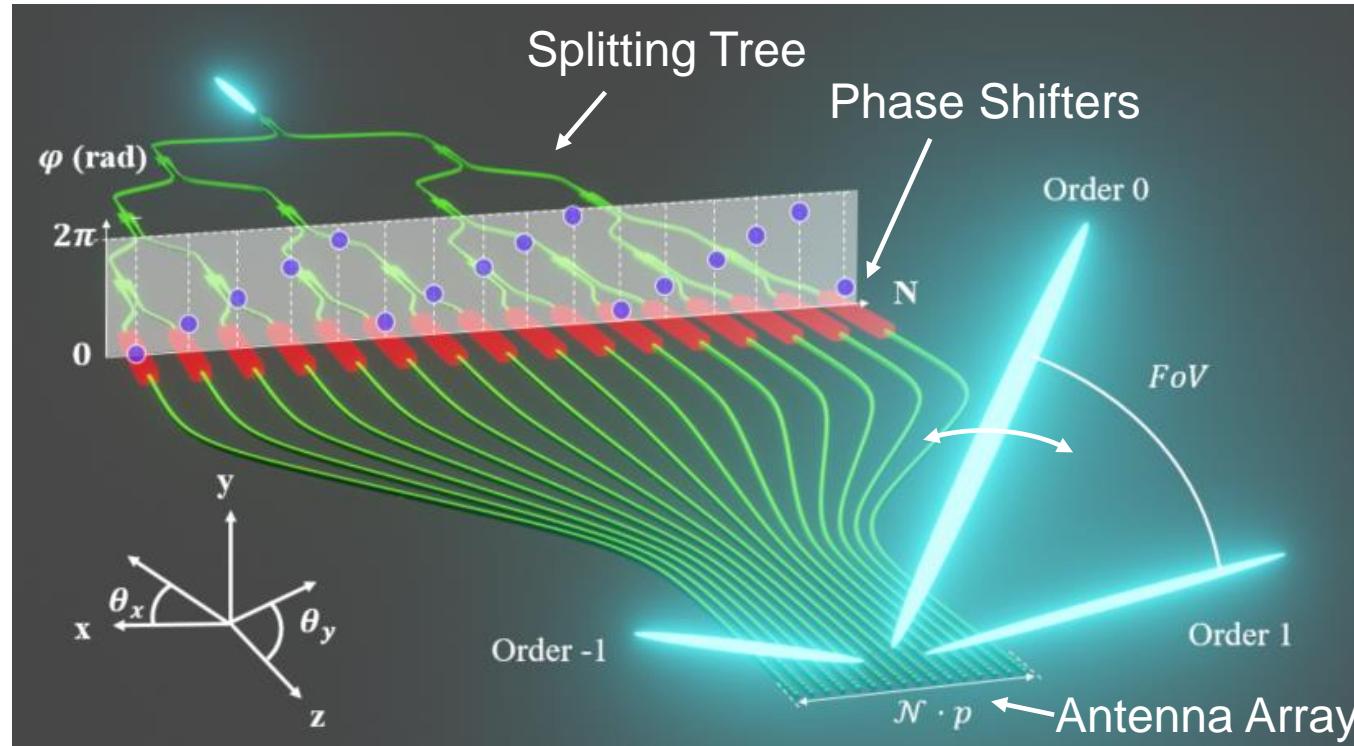


Silicon Photonics advantage

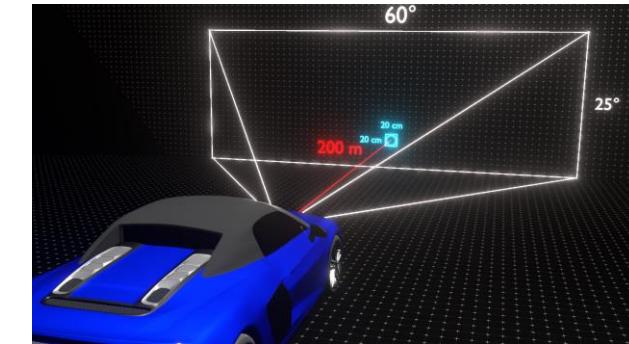
- Compatibility with eye-safe wavelength
- Non-mobile part beam scanner
- « Natural » compatibility with FMCW LiDAR by re-using telecom know how (coherent detection)
- No need of III-V SPAD in SWIR for photo detection
- LiDAR-on-chip

The example of OPA (Optical Phased Array)

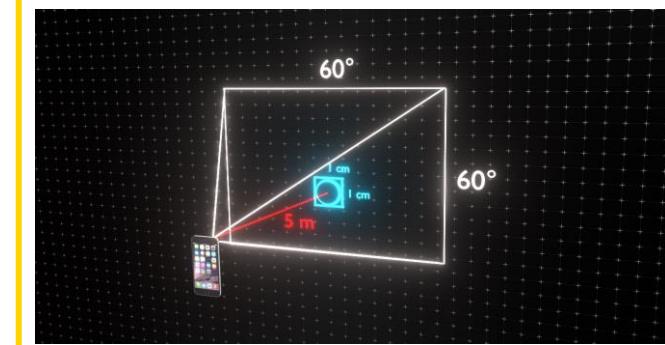
Constructive interference angle is controlled by array phase value



Automotive

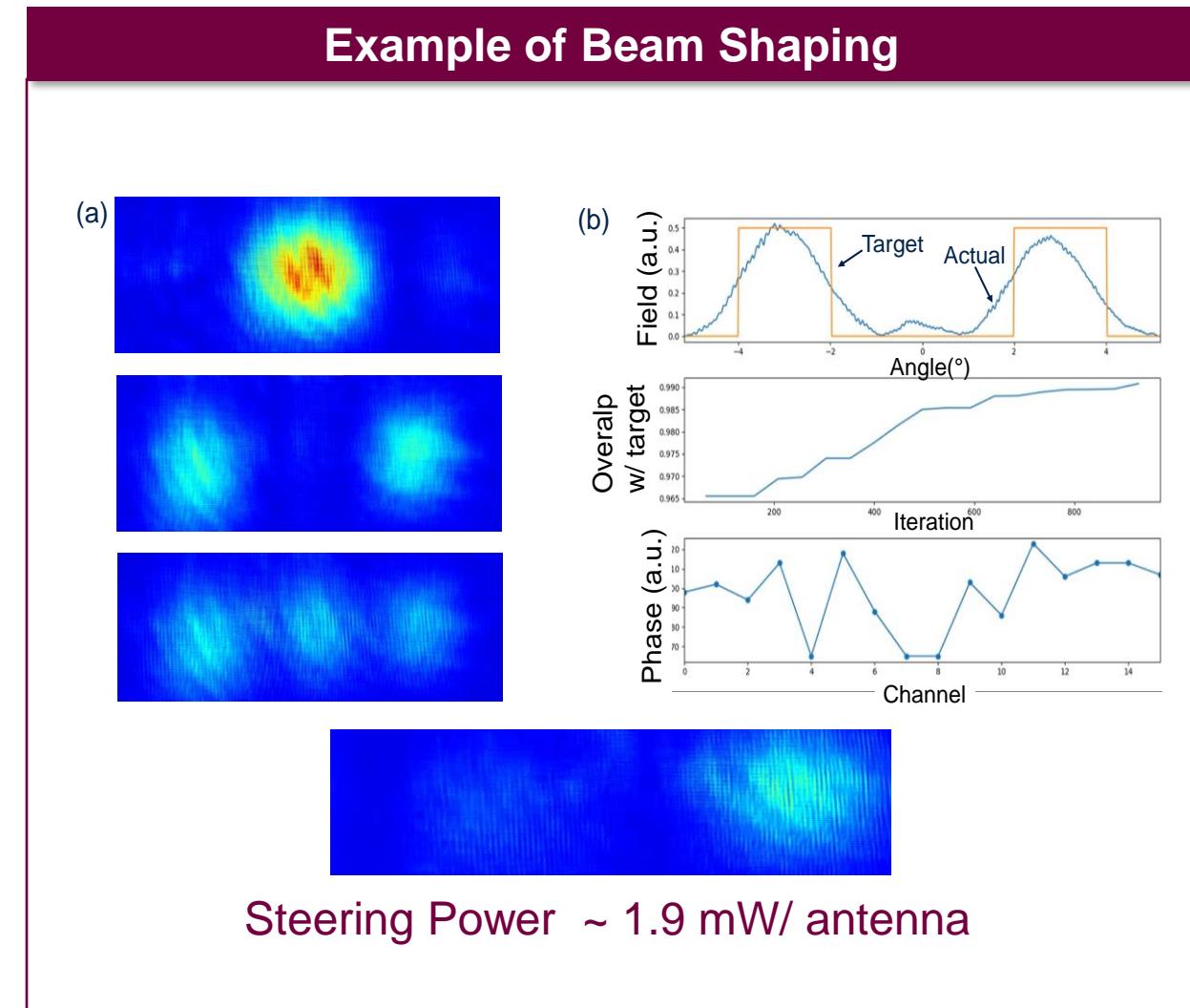
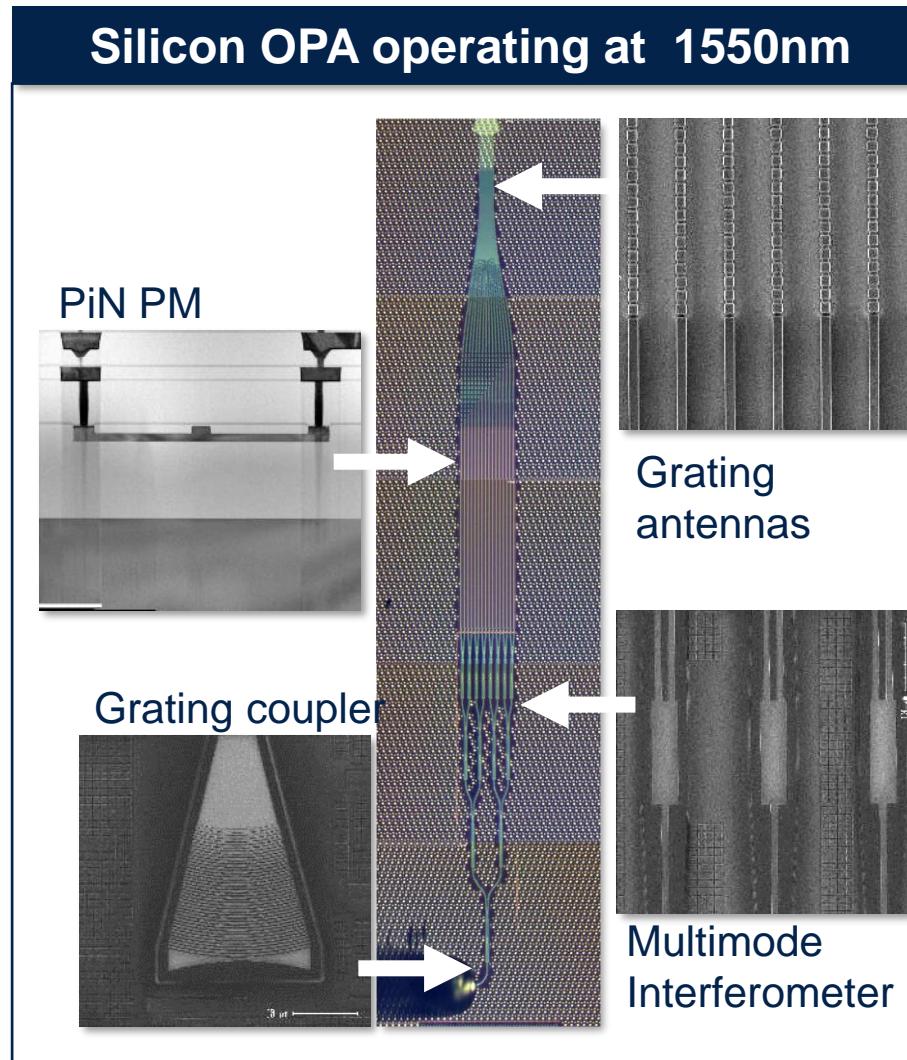


Mobile



1 mrad divergence, 60° FoV, 15 Hz framerate, and low power

16 channels Si-OPA, 16 PiN Phase Modulators



Low Power OPA challenge

Thermo-optics

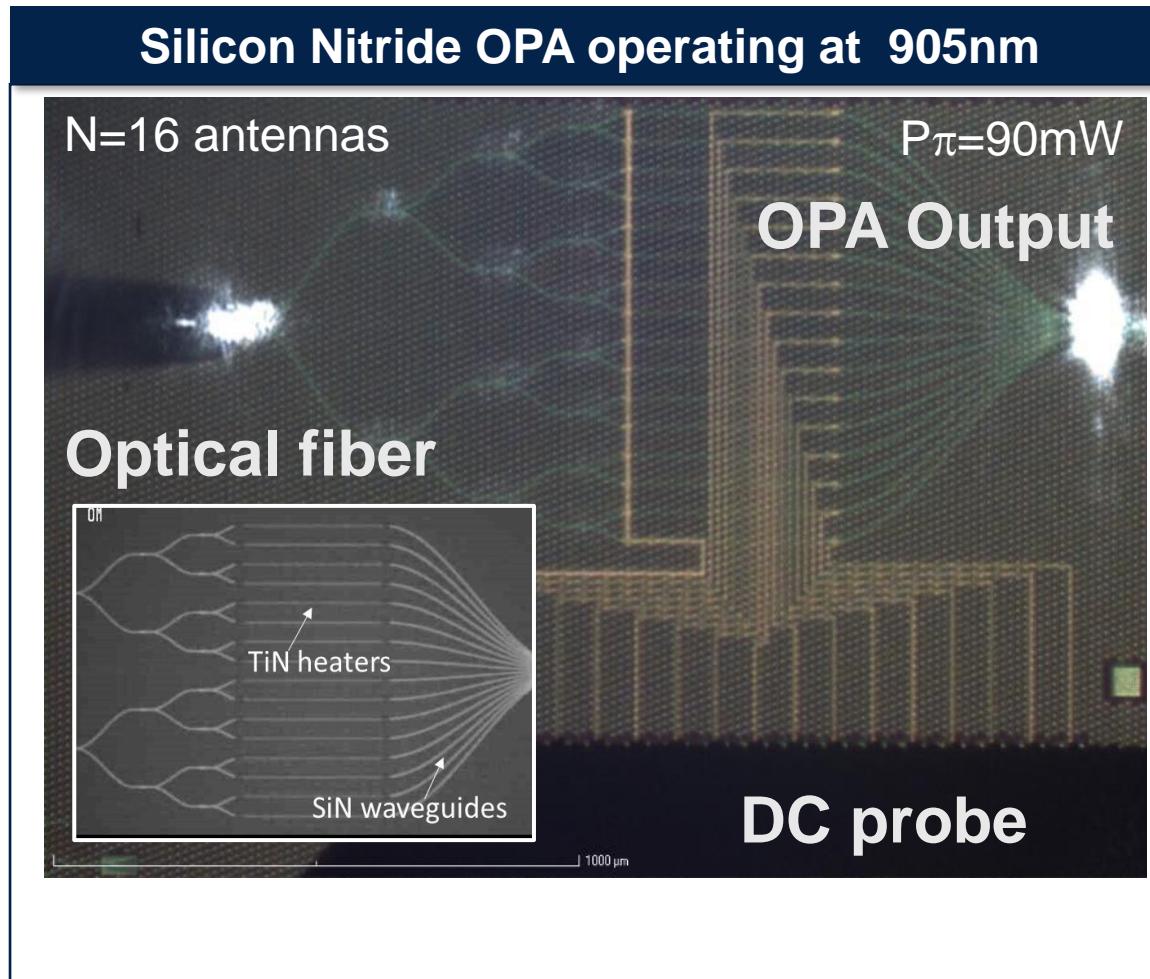
	Power consumption (P_π) / channel	Max Freq (Hz)	$L_{2\pi}$ (μm)	Total Steering Power for 512 antennas
Si Heater	~50 mW	~ 400kHz	~250	25W
TiN Heater (w/ SiN waveguides)	6* - 90mW <small>*=need air trenches</small>	~10KHz	~1000	3-45W
PiN Diode	~2 mW	~100MHz	~400	1W

Electro-optics

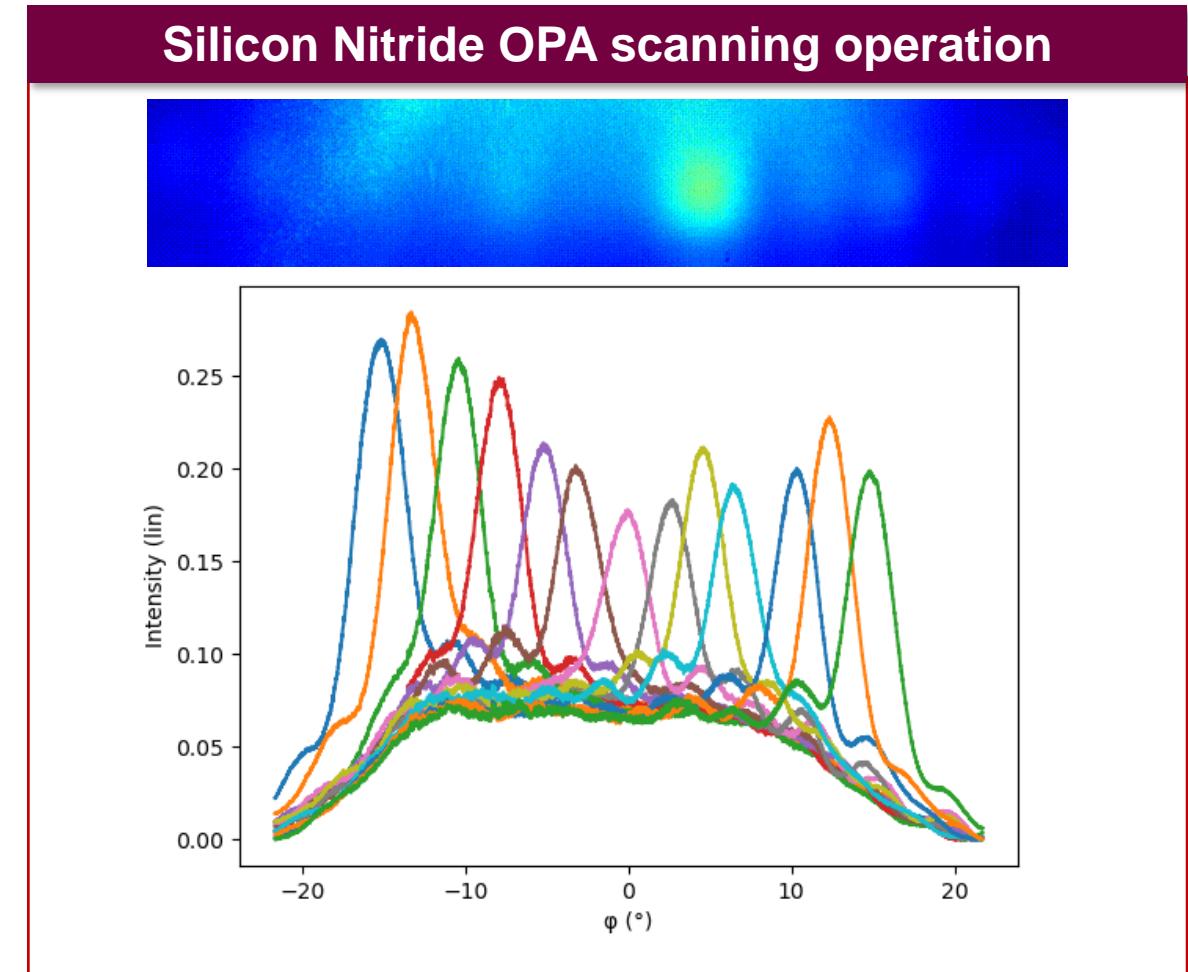
PN junction @1MHz	~0.01mW	>1GHz	~16000	5mW
Hybrid III-V/Si SISCAP @1MHz	~0.01mW	~1GHz	~1000	5mW

For low power OPA → EO modulation instead of TO
 BUT optical loss / decoherence = shortest as possible = high efficiency

SiN OPA operating at $\lambda=905\text{nm}$



S.Monfray et al. OFC 2022

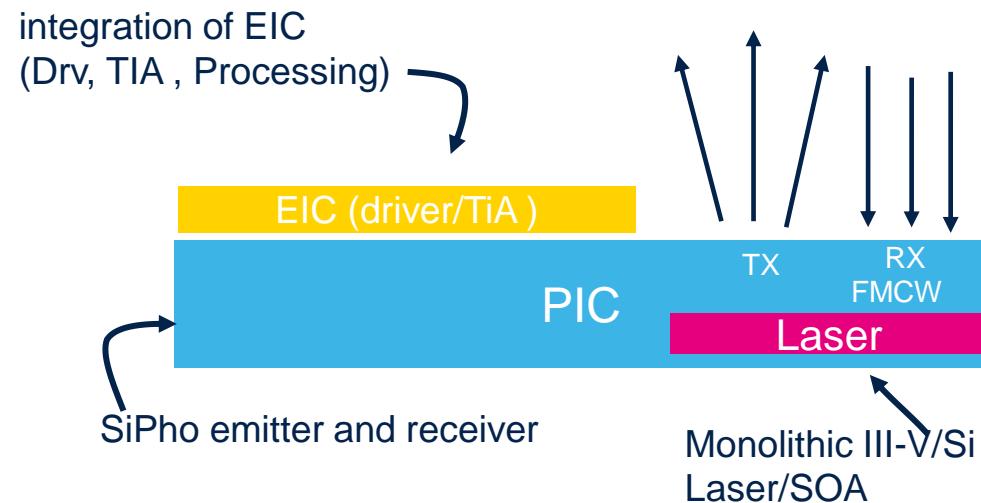


Research on III-V/Si Hybrid Integration

Source for 3D Imaging System using SiPho

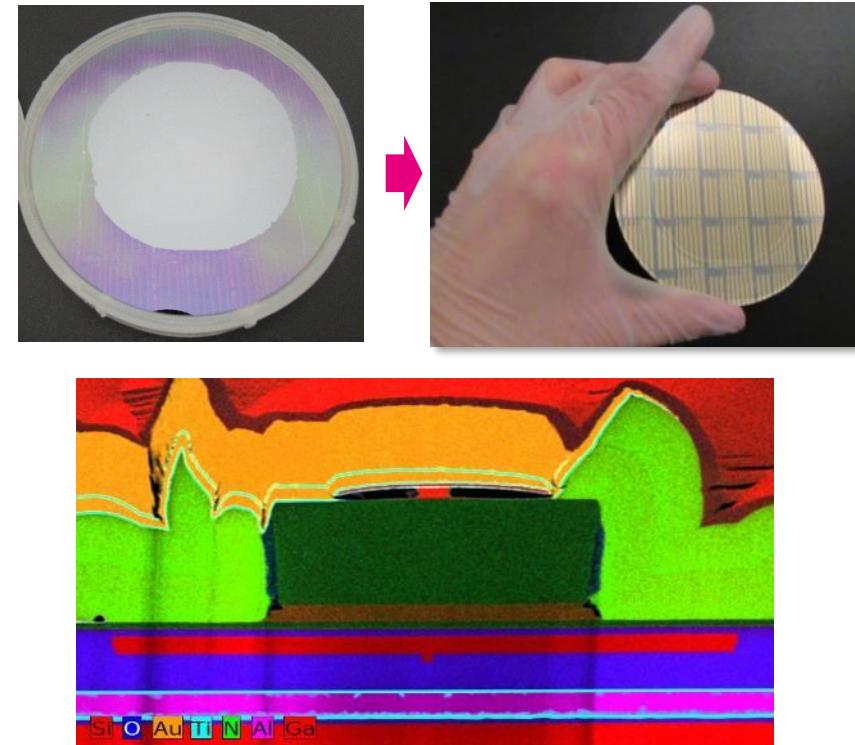
Adding intelligence to the laser source : FMCW and Scanning

Monolithic III-V/Si Laser Solution



Front side Laser integration : issue with BEOL topology
Back side Laser integration is the solution

Backside Laser Integration

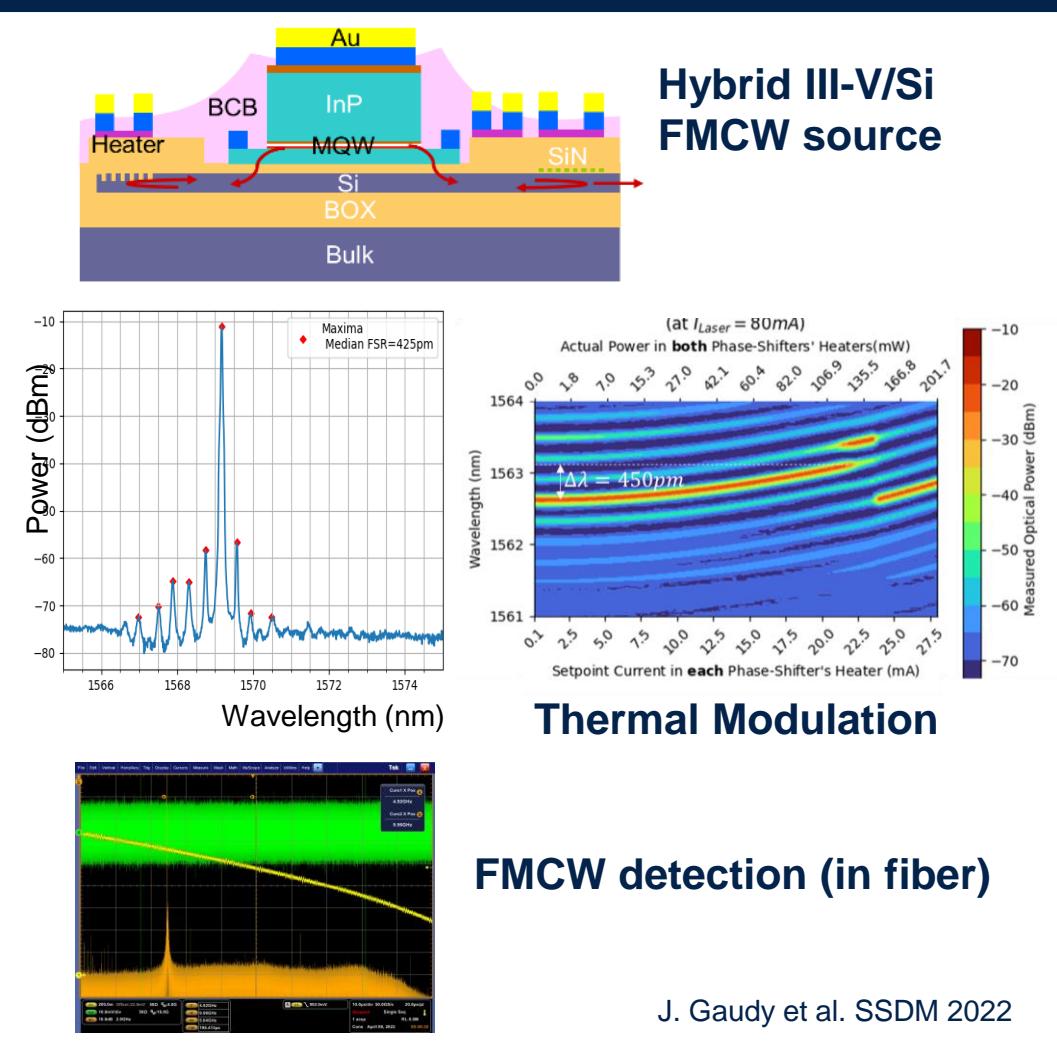


J. Durel et al. IEDM 2016 (ST/LETI/IMEP) , ST Patent

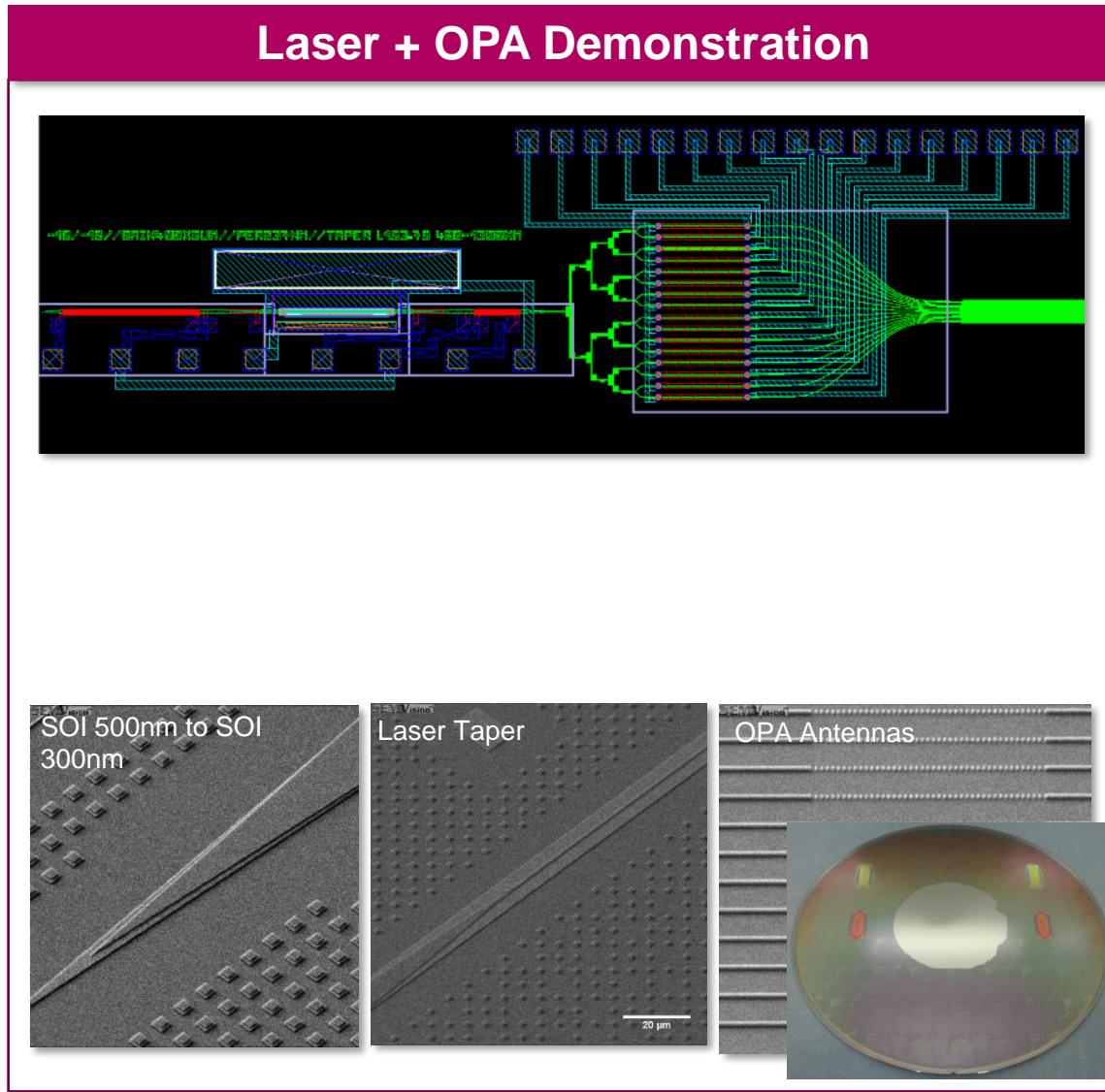
Next challenge : demonstrate Laser source integration on DAPHNE

FMCW Hybrid III-V/Si Source Prototype

Laser Prototype Principle



Laser + OPA Demonstration



Conclusion

- STMicroelectronics has developed Silicon Photonics technologies in 300mm
 - Mass production experience for data-communication
 - R&D for « beyond datacom » applications
- Partnership with universities for quantum applications
- Our current plan is to continue improving the technology to match the future challenges of datacom and sensing applications

Thank you

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